PPM 93-045

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Paramax Systems Corporation

Memorandum

PARAMAX A Unisys Company

PPM-93-045

DATE:

Mar. 23, 1993

TO:

J. Lohr/311.1 K. Sahu/300.1

FROM: SUBJECT: Radiation Report on ISTP/WAVES

Part No. M38510/11608BCA (DG307A)

Control No. 2105A

A. Sharma/311 cc:

Library/300.1

A radiation evaluation was performed on DG307A (Dual SPDT Switch) to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a Cobalt-60 gamma-ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation steps were 2.5, 5, 10, 15, 20 and 30 krads*. After the 20-krad irradiation, the parts were annealed at 25°C for 168 hours and then irradiated to 30 krads (cumulative). The dose rate was between 0.04 and 0.29 krads/hour, depending on the total dose level (see Table II for radiation schedule). After each radiation exposure and annealing treatment, parts were electrically tested at 25°C according to the test conditions and the specification limits** listed in Table III. These tests included one functional test at 10 kHz.

All ten parts passed initial (pre-rad) electrical tests. eight irradiated parts passed all electrical test up to and including the 5-krad irradiation level. At the 10-krad level, one part (S/N 54) exceeded the specification limits for Idoff1 of \pm 10.0 nA, with readings of -72.8 and 66.6 nA, and one part (S/N 59) marginally exceeeded the maximum specification limit of 70 ohms for Ron3, with a reading of 70.7 ohms. After the 15-krad irradiation, Five parts (S/N 53, 55, 57, 58 and 59) exceeded the maximum specification limits of 50.0 ohms for Ron1

^{*}The term rads, as used in this document, means rads(silicon). **These are manufacturers' non-irradiated data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time these tests were performed.

and 70.0 ohms for Ron3, with readings ranging from 50.6 to 57.6 ohms for Ron1 and 72.2 to 98.4 ohms for Ron3. S/N 54 continued to exceed the maximum specification limit of ± 10.0 nA for Idoff1, with a reading of 247.5 nA and also exceeded the maximum specification limit of ± 10 nA for Isoff1, with a reading of 117.5 nA. At the 20-krad level, five parts (S/N 53, 55, 57, 58 and 59) exceeded the maximum specification limits for Ron1 and Ron3 with readings ranging from 54.4 to 66.3 ohms for Ron1 and 85.5 to 140.0 ohms for Ron3. In addition, two parts (S/N 52 and 54 exceeded the specification limits for Idoff1, with readings of -11.5 and -677 nA, respectively, and one part (S/N 54 exceeded the specification limits for Isoff1, with a reading of 140 nA.

After the 20-krad irradiation, the parts were annealed for 168 hours at 25°C. After annealing, seven parts (S/N 52, 53, 55, 56, 57 58 and 59) exceeded the maximum specification limits for Ron1 and Ron3, with readings ranging from 51.3 to 69.9 ohms for Ron1 and 72.0 to 203 ohms for Ron3. One part (S/N 56) recovered to within specification limits for Ron1.

At the 30-krad level, seven parts (S/N 52, 53, 55, 56, 57, 58 and 59) exceeded the maximum specification limits for Ron1 and Ron3, with readings ranging from 51.6 to 72.8 ohms for Ron1 and 75.7 to 324 ohms for Ron3. In addition, one part (S/N 54) exceeded the specification limits for Idoff1, with a reading of -12.5 nA.

After the 30-krad irradiation, the parts were annealed at 100°C for 168 hours to observed rebound effects. Four parts (S/N 53, 55, 57 and 59) showed some rebound effect for Ron3, with readings of 1.78 Kohms and one part (S/N 53) exceeded the maximum specification limit of 70 ohms for Ron4, with a reading of 1.9 Kohms.

All Parts passed the functional test throughout all irradiation and annealing steps. No significant changes were observed in any other parameters throughout all irradiation and annealing steps.

Table IV provides a summary of the mean and standard deviation values for each parameter after different irradiation exposures and annealing steps.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

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TABLE I. Part Information

Generic Part Number: DG307A

M38510/11608BCA* Part Number:

ISTP/WAVES

2105A Control Number:

C33260 Charge Number:

Siliconix Manufacturer:

9224A Lot Date Code:

Quantity Tested: 10

Serial Numbers of

52, 53, 54, 55, 56, 57, 58, 59 Radiation Samples:

Serial Numbers of control Samples:

50, 51

Part Function:

Dual SPDT Switch

Part Technology:

CMOS

Package Style:

14-lead DIP package

Test Equipment:

3260

Test Engineer:

T. Mondy

^{*} No radiation tolerance/hardness was guaranteed by the manufacturer for this part.

TABLE II. Radiation Schedule for DG307A

EVENTS	DATE
	02/17/93
1) INITIAL ELECTRICAL MEASUREMENTS	02/18/93
2) 2.5 KRAD IRRADIATION (0.14 KRADS/HOUR) POST-2.5 KRAD ELECTRICAL MEASUREMENT	02/19/93
3) 5 KRAD IRRADIATION (0,04 KRADS/HOUR) POST-5 KRAD ANNEAL ELECTRICAL MEASUREMENTS	02/19/93 02/22/93
4) 10 KRAD IRRADIATION (0.25 KRADS/HOUR) POST-10 KRAD ELECTRICAL MEASUREMENTS	02/22/93 02/23/93
5) 15 KRAD IRRADIATION (0.26 KRADS/HOUR) POST-15 KRAD ANNEAL ELECTRICAL MEASUREMENTS	02/28/93 02/25/93
	02/25/93
6) 20 KRAD IRRADIATION (0.29 KRADS/HOUR) POST-20 KRAD ELECTRICAL MEASUREMENTS	02/26/93
	02/26/93
7) 168 HOUR ANNEALING @25°C POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENTS	03/05/93
8) 30 KRAD IRRADIATION (0.15 KRADS/HOUR)	03/05/93
POST-30 KRAD ELECTRICAL MEASUREMENTS	03/09/93
A TO MOUTO ANNEATING 6100°C	03/08/93
9) 168 HOUR ANNEAL ELECTRICAL MEASUREMENTS	03/16/93

ALL ELECTRICAL MEASUREMENTS WERE PERFORMED AT 25°C.

PARTS WERE IRRADIATED AND ANNEALED UNDER BIAS; SEE FIGURE 1.

Table III. Electrical Characteristics of DG307A

		Specifica Limi	ation ts							
Test Units		Min	Max	Conditions						
FUNC1	P/F			Vd = 15, 0 V, f = 10 kHz						
 Ron 1	ohms	0	50	Vd = -10 V, Is = -10 mA						
Ron2	ohms	0	50	Vd = 10 V, Is = -10 mA						
Ron3	ohms	0	70	$\pm V = \pm 10V$, $Vd = -7.5V$, $Is = +10mA$						
Ron4	ohms	0	70	<u>+</u> V= <u>+</u> 10V, Vd=+7.5V, Is=-10mA						
Idon1	nA	-10*	10*	Vd = + 14 V, Vs = + 14 V						
Idoff1	nA	-10*	10*	Vd = + 14 V, Vs = - 14 V						
Isoff1	nA	-10*	10*	H 18						
IIL	uA	-1.0	0	Vin = 0 V						
IIH	uA	0	1.0	Vin = 15 V						
	uA	0	10.0	\pm V = \pm 15 V, Logic = 0 V						
ICCP1	uA	-10	0	11						

^{*}Specified at \pm 1 nA and \pm 2 nA, but due to ATE limitation, these limits can only be checked at \pm 10 nA. Currents less than \pm 3 nA are forced to zero.

TABLE IV: Summary of Electrical Measurements After Total Dose Exposures and Annealing Steps for DG307A 1/

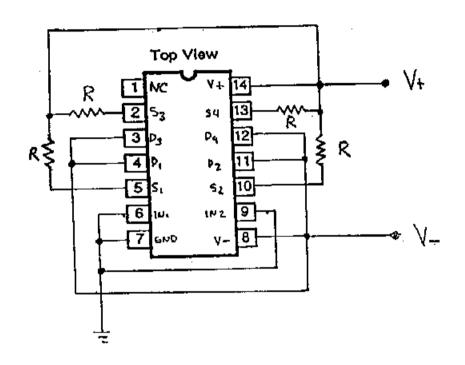
					Total Dose Exposure (krads)									Anneal		TDE		Anneal		
,	Spec.	ĺ			Total D		Jose Expos		10		15		20		168 hrs @25°C		30 krads		158 @100	
	Līm./	2	Pre-	_		sđ	mean	sđ	mean	sđ	mean	sđ	mean	sd	mean	sd	mean	вd	mean	sđ
Parameters FUNC 10KhZ			mean PASS		mean PASS		PASS		PASS		PASS		PASS 46.5	11	PASS 48.0		PASS 50.4	14	PASS 49.5	16
Ronl ohms	0	50	29.0	1.:	31.0 28.3	1 2	34.3	$\frac{2.2}{3.1}$	39.4 34.9	5.2 4.3	43°3 37.5		39.6	4.2	39.3	4.0	41.6	3.9	35 3	5.4
lon2 ohms	0	50 70	26.7 39.2	1.1	41.4	1.5	46.0	4.9	52.6	10	59.5	19	72,2 61.9	32 3.8	84.4 50.1	51 2.8	103 65.5	3.6	456 396	73
Ren4 ohms		70	585	. 78	41.9	2.6	46.4	$\frac{4\cdot 1}{1}$	51:6 05	.42	56.8 08	.86	-,33		- 10		- 52	1.2 3.9	0.02	.80
idoni na Idoffi/3 na		10	0	0	0	0_	0	1.2	*.17	14	50 20,2	95	-1.1 34.6	121 187	0.51	$\frac{1.2}{1.5}$	58 1.74		0.	
Isoff1/3 r.A	·· ·	10	0	0	0	0	0.52	0	0.01	0.1	0	- 0	Ö	0	Q	. 0	0	0	0	0
IIL UA IIH UA		1	0	0	0 /	ŏ	0	0	0	0	0	<u>0</u>	0.123	<u>0</u> .85	0.01	0	0.01	.02		.9
ICCP1 uA	0	10	0	0	0	- 0 -	0.01	0	0.08 09	.29	0,13 15	.57	-,24		01		02	.02	0	.3

Notes:

- 1/ The mean and standard deviation values were calculated over the eight parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.
- 2/ These are manufacturers' non-irradiated data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time the tests were performed.
- 3/ After the 10-krad irradiation, values of Idoffl and Isoffi ranged from -677 nA to 248 nA. The mean values are not calculated from absolute values of the data, therefore, the mean does not reflect the actual range of values. The standard deviation, however, indicates the range of readings.

Radiation sensitive parameters were Ron1, Iccn1, Idoff1 and Isoff1.

Figure 1. Radiation Bias Circuit for DG307A



Ta = 25°C

 $V+ = 15.0 \text{ VDC} \pm 0.5 \text{ VDC}$

 $V = -15.0 \text{ VDC} \pm 0.5 \text{ VDC}$

R = 3.3 Kohms